

2SC4132 / 2SD1857

- 1) High breakdown voltage. ($V_{CEO} = 120V$)
- 2) Low collector output capacitance.
(Typ. 20pF at $V_{CB} = 10V$)
- 3) High transition frequency. ($f_T = 80MHz$)
- 4) Complements the 2SB1236.

Parameter		Symbol	Limits	Unit
Collector-base voltage		V _{CB0}	120	V
Collector-emitter voltage		V _{CE0}	120	V
Emitter-base voltage		V _{EB0}	5	V
Collector current		I _C	2	A
		I _{CP}	3	A *1
Collector power dissipation	2SC4132 2SD1857	P _C	0.5	W *2
			2	
			1	
Junction temperature		T _J	150	°C
Storage temperature		T _{stg}	-55~+150	°C

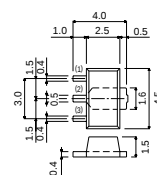
*₁ Single pulse Pw = 10ms

*2 When mounted on a 40 × 40 × 0.7mm ceramic board.

Type	2SC4132	2SD1857
Package	MPT3	ATV
hFE	PQR	PQR
Marking	CB*	—
Code	T100	TV2
Basic ordering unit (pieces)	1000	2500

* Denotes h_{EE}

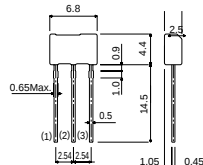
2SC4132



ROHM : MPT3
EIAJ : SC-62

- (1) Base(Gate)
- (2) Collector(Drain)
- (3) Emitter(Source)

2SD1857



Taping specifications

- (1) Emitter
- (2) Collector
- (3) Base

ROHM : ATV

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	V_{CB0}	120	—	—	V	$I_C = 50\mu A$
Collector-emitter breakdown voltage	V_{CE0}	120	—	—	V	$I_C = 1mA$
Emitter-base breakdown voltage	V_{EB0}	5	—	—	V	$I_E = 50\mu A$
Collector cutoff current	I_{C0}	—	—	1	μA	$V_{CB} = 100V$
Emitter cutoff current	I_{E0}	—	—	1	μA	$V_{EB} = 4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	0.4	V	$I_C/I_E = 1A/0.1A$
DC current transfer ratio	h_{FE}	82	—	390	—	$V_{CE}/I_C = 5V/0.1A$
Transition frequency	f_T	80	—	—	MHz	$V_{CE} = 5V, I_E = -0.1A, f = 30MHz$
Output capacitance	C_{ob}	20	—	—	pF	$V_{CB} = 10V, I_E = 0A, f = 1MHz$

* Measured using pulse current.

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Datasheets for electronics components.